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IV Semester M.Sc. Degree (CBSS-Reg./Suppl./Imp.) and ISMV (S. A. Examination, April 2020 (E.) to Inucoos as avið (d. (2014 Admission Onwards) moltulove erti nislox 3 (o **PHYSICS** 

PHY 4E06: Optoelectronics

Time: 3 Hours stems to seem priviseer tripil evites as and ebolooto Max. Marks: 60

## SECTION - A lorid is sets energ if the blont at

Answer both questions (either a or b).

- 1. a) i) Sketch and explain the reverse biased pn junction with minority carrier profiles and the origin of the reverse current.
  - ii) Explain the depletion layer capacitance. Swood solution approve vilso s

incident per day is about 6kWhm? and a photovoltaic dego; that converts

- b) What is Mode Locking? Deduce the expressions for the Separation between pulses  $\Delta t_{sep}$  and pulse width  $\Delta t_{n}$  for a mode locked laser.
- 2. a) What is Pockels effect? With a diagram explain the principle and operation of a transverse Pockels cell phase modulator.

- e) With a sketch explain the principle and working of a Kerr cell phase b) i) Explain the principle and operation of a pn junction photodiode.
  - ii) Give an account of PIN photodiode.

## b) Briefly explain the phase matches Property

Answer any four.

(1 mark for Part a, 3 marks for Part b, 5 marks for Part c).

- 3. a) In which bands do the movement of electrons and holes takes place?
  - b) Sketch the energy band diagram of an n-type Si-doped with 1 ppm As.

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- c) Consider a GaAs LED, the band gap of GaAs at 300K is 1.42eV, which changes (decreases) with temperature as  $dE_g/dT = -4.5 \times 10^{-4} \text{ eVK}^{-1}$ . What is the change in the emitted wavelength if the temperature change is 10°C?
- 4. a) What is meant by active mode locking? ped .52.M refeemed VI
  - b) Give an account of LED materials. A moissimex3
  - c) Explain the evolution of a giant pulse through Q-switching.
- 5. a) What is a avalanche photodiode?
  - b) Explain the principle and operation of a phototransistor.
- c) A Si PIN photodiode has an active light receiving area of diameter 0.4mm. When radiation of wavelength 700nm (red light) and intensity 0.1m Wcm<sup>-2</sup> is incident it generates a photocurrent of 56.6nA. What is the responsivity and quantum efficiency of the photodiode at 700nm.
- 6. a) What are photovoltaic devices?
  - b) With a sketch explain the principle and operation of a solar cell.
  - c) A particular family house in a sunny geographic location over a year consumes a daily average electrical power of 500W. If the annual average Solar intensity incident per day is about 6kWhm<sup>-2</sup> and a photovoltaic device that converts solar energy to electrical energy has an efficiency of 15%. What is the required device area?
- 7. a) What is dichroism?
  - b) Distinguish between quarter wave plate retarder and half wave plate retarder.
  - c) With a sketch explain the principle and working of a Kerr cell phase modulator.
- 8. a) What is meant by second harmonic generation?
  - b) Briefly explain the phase matching.
  - c) Give an account of third order nonlinear optical process. (4×9=36)

(1 mark for Part a, 2 marks for Part b, 5 marks